

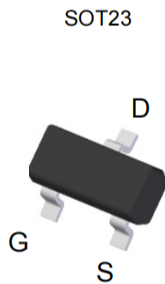
### Product Summary

- $V_{DS} = 60V, I_D = 0.3A$   
 $R_{DS(ON)} < 2.5 \Omega @ V_{GS}=4.5V$   
 $R_{DS(ON)} < 2.2 \Omega @ V_{GS}=10V$
- ESD Rating : HBM 2000V

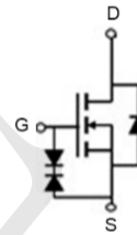
### Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays

### Package and Pin Configuration



### Circuit diagram



### Marking: 7002

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 150^\circ C$ )	$I_D$	$T_A = 25^\circ C$	0.3
		$T_A = 100^\circ C$	0.19
Drain Current-Pulsed (Note 1)	$I_{DM}$	1.5	A
Maximum Power Dissipation	$P_D$	0.35	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

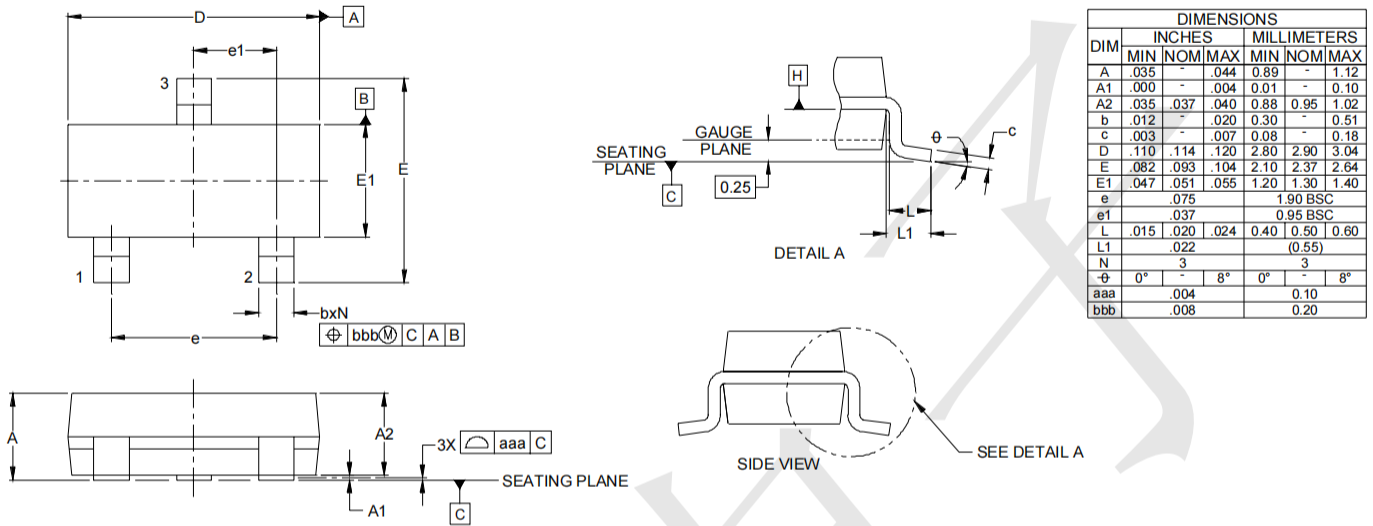
### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	$^\circ C/W$
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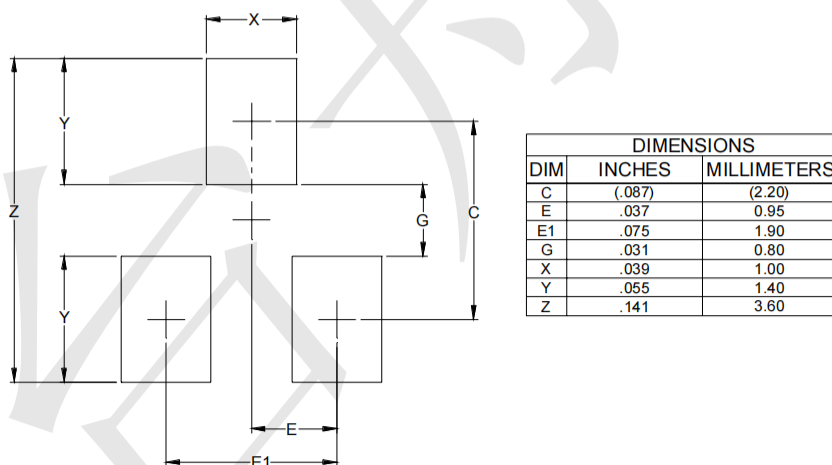
**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 1$	$\mu A$
		$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.2A$	-	1.9	2.5	$\Omega$
		$V_{GS}=10V, I_D=0.3A$	-	1.8	2.2	$\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=0.2A$	0.1	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$		27		PF
Output Capacitance	$C_{oss}$			18		PF
Reverse Transfer Capacitance	$C_{rss}$			2		PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=0.2A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	10	-	nS
Turn-on Rise Time	$t_r$		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=0.3A,$ $V_{GS}=4.5V$	-	1.7	3	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=0.2A$	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	0.3	A

**SOT23 - Package Outline Drawing**



**Suggested Land Pattern**



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